



# Thyristor Module

$V_{RRM} = 2 \times 1600 \text{ V}$

$I_{TAV} = 200 \text{ A}$

$V_T = 1.12 \text{ V}$

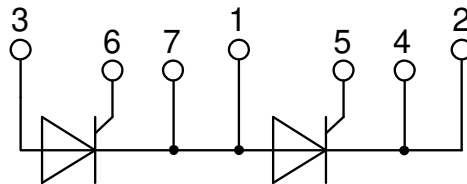
Phase leg

Part number

**MCMA200P1600YA**



Backside: isolated



### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al<sub>2</sub>O<sub>3</sub>-ceramic

### Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: Y4

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

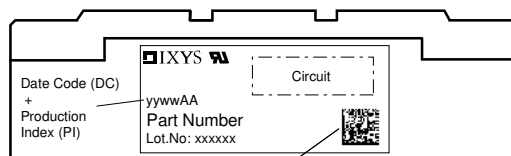
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| Thyristor      |  |  |                         | Ratings |       |                   |  |
|----------------|--|--|-------------------------|---------|-------|-------------------|--|
| Symbol         | Definition   | Conditions   | min.                    | typ.    | max.  | Unit              |  |
| $V_{RSM/DSM}$  | max. non-repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}C$   |                         |         | 1700  | V                 |  |
| $V_{RRM/DRM}$  | max. repetitive reverse/forward blocking voltage     | $T_{VJ} = 25^{\circ}C$   |                         |         | 1600  | V                 |  |
| $I_{R/D}$      | reverse current, drain current                       | $V_{R/D} = 1600 V$   | $T_{VJ} = 25^{\circ}C$  |         | 300   | $\mu A$           |  |
|                |  | $V_{R/D} = 1600 V$   | $T_{VJ} = 125^{\circ}C$ |         | 10    | mA                |  |
| $V_T$          | forward voltage drop                                 | $I_T = 200 A$  | $T_{VJ} = 25^{\circ}C$  |         | 1.17  | V                 |  |
|                |  | $I_T = 400 A$  |                         |         | 1.40  | V                 |  |
|                |  | $I_T = 200 A$  | $T_{VJ} = 125^{\circ}C$ |         | 1.12  | V                 |  |
|                |  | $I_T = 400 A$  |                         |         | 1.41  | V                 |  |
| $I_{TAV}$      | average forward current                              | $T_C = 85^{\circ}C$  | $T_{VJ} = 125^{\circ}C$ |         | 200   | A                 |  |
| $I_{T(RMS)}$   | RMS forward current                                  | 180° sine  |                         |         | 315   | A                 |  |
| $V_{T0}$       | threshold voltage                                    | } for power loss calculation only  | $T_{VJ} = 125^{\circ}C$ |         | 0.83  | V                 |  |
| $r_T$          | slope resistance                                     |  |                         |         | 1.43  | m $\Omega$        |  |
| $R_{thJC}$     | thermal resistance junction to case                  |  |                         |         | 0.17  | K/W               |  |
| $R_{thCH}$     | thermal resistance case to heatsink                  |  |                         | 0.09    |       | K/W               |  |
| $P_{tot}$      | total power dissipation                              |  | $T_C = 25^{\circ}C$     |         | 680   | W                 |  |
| $I_{TSM}$      | max. forward surge current                           | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$   | $T_{VJ} = 45^{\circ}C$  |         | 6.00  | kA                |  |
|                |  | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$  | $V_R = 0 V$             |         | 6.48  | kA                |  |
|                |  | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$   | $T_{VJ} = 125^{\circ}C$ |         | 5.10  | kA                |  |
|                |  | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$  | $V_R = 0 V$             |         | 5.51  | kA                |  |
| $I^2t$         | value for fusing                                     | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$   | $T_{VJ} = 45^{\circ}C$  |         | 180.0 | kA <sup>2</sup> s |  |
|                |  | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$  | $V_R = 0 V$             |         | 174.7 | kA <sup>2</sup> s |  |
|                |  | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$   | $T_{VJ} = 125^{\circ}C$ |         | 130.1 | kA <sup>2</sup> s |  |
|                |  | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$  | $V_R = 0 V$             |         | 126.3 | kA <sup>2</sup> s |  |
| $C_J$          | junction capacitance                                 | $V_R = 400 V \quad f = 1 \text{ MHz}$  | $T_{VJ} = 25^{\circ}C$  |         | 273   | pF                |  |
| $P_{GM}$       | max. gate power dissipation                          | $t_p = 30 \mu s$   | $T_C = 125^{\circ}C$    |         | 120   | W                 |  |
|                |  | $t_p = 500 \mu s$  |                         |         | 60    | W                 |  |
| $P_{GAV}$      | average gate power dissipation                       |  |                         |         | 8     | W                 |  |
| $(di/dt)_{cr}$ | critical rate of rise of current                     | $T_{VJ} = 140^{\circ}C; f = 50 \text{ Hz}$ repetitive, $I_T = 600 A$   |                         |         | 100   | A/ $\mu s$        |  |
|                |  | $t_p = 200 \mu s; di_G/dt = 0.5 A/\mu s;$<br>$I_G = 0.5 A; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 200 A$              |                         |         | 1000  | A/ $\mu s$        |  |
| $(dv/dt)_{cr}$ | critical rate of rise of voltage                     | $V = \frac{2}{3} V_{DRM}$  | $T_{VJ} = 140^{\circ}C$ |         | 1000  | V/ $\mu s$        |  |
|                |  | $R_{GK} = \infty$ ; method 1 (linear voltage rise)   |                         |         |       |                   |  |
| $V_{GT}$       | gate trigger voltage                                 | $V_D = 6 V$  | $T_{VJ} = 25^{\circ}C$  |         | 2.5   | V                 |  |
|                |  |  | $T_{VJ} = -40^{\circ}C$ |         | 2.6   | V                 |  |
| $I_{GT}$       | gate trigger current                                 | $V_D = 6 V$  | $T_{VJ} = 25^{\circ}C$  |         | 150   | mA                |  |
|                |  |  | $T_{VJ} = -40^{\circ}C$ |         | 200   | mA                |  |
| $V_{GD}$       | gate non-trigger voltage                             | $V_D = \frac{2}{3} V_{DRM}$  | $T_{VJ} = 125^{\circ}C$ |         | 0.2   | V                 |  |
| $I_{GD}$       | gate non-trigger current                             |  |                         |         | 10    | mA                |  |
| $I_L$          | latching current                                     | $t_p = 30 \mu s$   | $T_{VJ} = 25^{\circ}C$  |         | 300   | mA                |  |
|                |  | $I_G = 0.5 A; di_G/dt = 0.5 A/\mu s$   |                         |         |       |                   |  |
| $I_H$          | holding current                                      | $V_D = 6 V \quad R_{GK} = \infty$  | $T_{VJ} = 25^{\circ}C$  |         | 200   | mA                |  |
| $t_{gd}$       | gate controlled delay time                           | $V_D = \frac{1}{2} V_{DRM}$  | $T_{VJ} = 25^{\circ}C$  |         | 2     | $\mu s$           |  |
|                |  | $I_G = 0.5 A; di_G/dt = 0.5 A/\mu s$   |                         |         |       |                   |  |
| $t_q$          | turn-off time  | $V_R = 100 V; I_T = 200 A; V = \frac{2}{3} V_{DRM}$<br>$di/dt = 10 A/\mu s \quad dv/dt = 20 V/\mu s \quad t_p = 200 \mu s$ | $T_{VJ} = 100^{\circ}C$ |         | 150   | $\mu s$           |  |



| Package Y4    |  |                      |      | Ratings |      |      |  |
|---------------|--|----------------------|------|---------|------|------|--|
| Symbol        | Definition   | Conditions           | min. | typ.    | max. | Unit |  |
| $I_{RMS}$     | RMS current  | per terminal         |      |         | 300  | A    |  |
| $T_{VJ}$      | virtual junction temperature                                 |                      | -40  |         | 125  | °C   |  |
| $T_{op}$      | operation temperature  |                      | -40  |         | 100  | °C   |  |
| $T_{stg}$     | storage temperature  |                      | -40  |         | 125  | °C   |  |
| <b>Weight</b> |  |                      |      |         | 150  | g    |  |
| $M_D$         | mounting torque  |                      | 2.25 |         | 2.75 | Nm   |  |
| $M_T$         | terminal torque  |                      | 4.5  |         | 5.5  | Nm   |  |
| $d_{Spp/App}$ | creepage distance on surface   striking distance through air | terminal to terminal | 14.0 | 10.0    |      | mm   |  |
| $d_{Spb/Apb}$ |  | terminal to backside | 16.0 | 16.0    |      | mm   |  |
| $V_{ISOL}$    | isolation voltage  | t = 1 second         | 3600 |         |      | V    |  |
|               |  | t = 1 minute         | 3000 |         |      | V    |  |



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

**Part description**

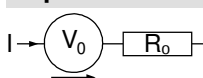
- M = Module
- C = Thyristor (SCR)
- M = Thyristor
- A = (up to 1800V)
- 200 = Current Rating [A]
- P = Phase leg
- 1600 = Reverse Voltage [V]
- YA = Y4-M6

| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-----------------|--------------------|---------------|----------|----------|
| Standard | MCMA200P1600YA  | MCMA200P1600YA     | Box           | 6        | 524795   |

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 125\text{ °C}$

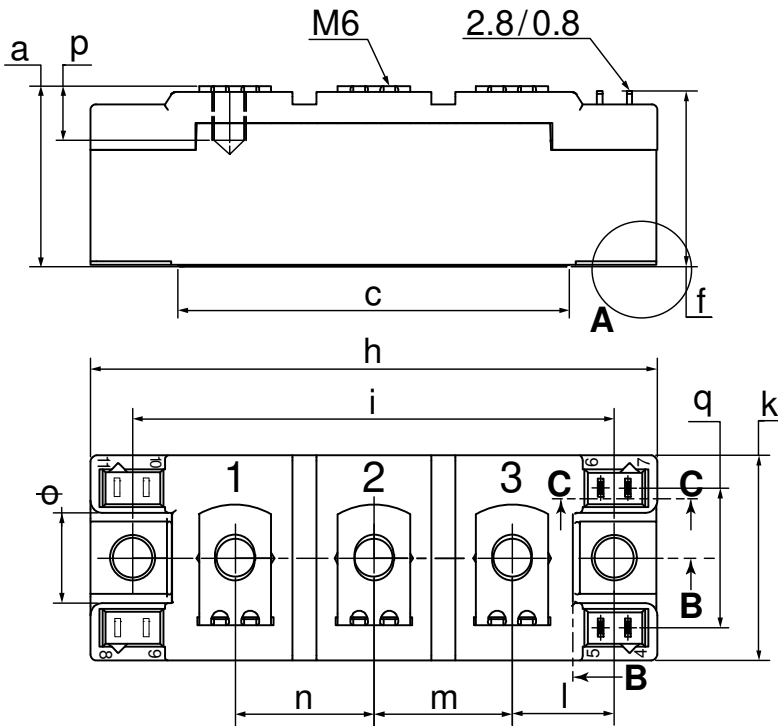


**Thyristor**

|              |                    |      |    |
|--------------|--------------------|------|----|
| $V_{0\ max}$ | threshold voltage  | 0.83 | V  |
| $R_{0\ max}$ | slope resistance * | 0.8  | mΩ |

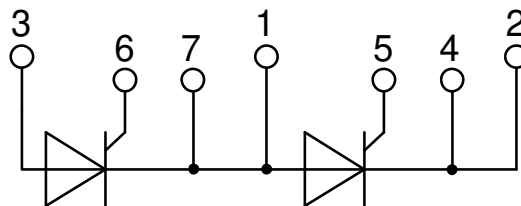
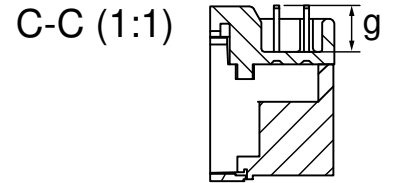
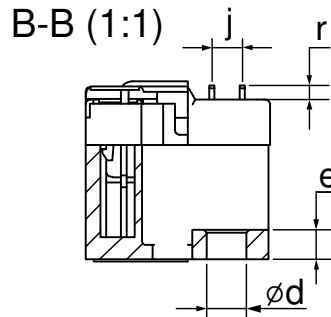
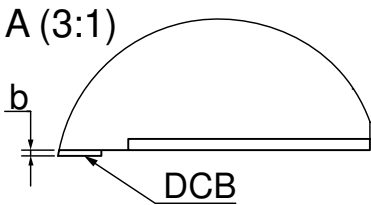


**Outlines Y4**



| Dim. | MIN [mm]  | MAX [mm] | MIN [inch] | MAX [inch] |
|------|-----------|----------|------------|------------|
| a    | 30.0      | 30.6     | 1.181      | 1.205      |
| b    | typ. 0.25 |          | typ. 0.010 |            |
| c    | 64.0      | 65.0     | 2.520      | 2.559      |
| d    | 6.5       | 7.0      | 0.256      | 0.275      |
| e    | 4.9       | 5.1      | 0.193      | 0.201      |
| f    | 28.6      | 29.2     | 1.126      | 1.150      |
| g    | 7.3       | 7.7      | 0.287      | 0.303      |
| h    | 93.5      | 94.5     | 3.681      | 3.720      |
| i    | 79.5      | 80.5     | 3.130      | 3.169      |
| j    | 4.8       | 5.2      | 0.189      | 0.205      |
| k    | 33.4      | 34.0     | 1.315      | 1.339      |
| l    | 16.7      | 17.3     | 0.657      | 0.681      |
| m    | 22.7      | 23.3     | 0.894      | 0.917      |
| n    | 22.7      | 23.3     | 0.894      | 0.917      |
| o    | 14.0      | 15.0     | 0.551      | 0.591      |
| p    | typ. 10.5 |          | typ. 0.413 |            |
| q    | 22.8      | 23.3     | 0.898      | 0.917      |
| r    | 1.8       | 2.4      | 0.071      | 0.041      |

Optional accessories for modules  
 Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red  
 Type ZY 180L (L = Left for pin pair 4/5)  
 Type ZY 180R (R = Right for pin pair 6/7) } UL 758, style 3751



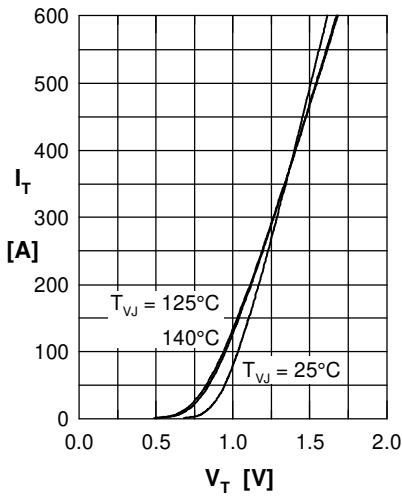
**Thyristor**


Fig. 1 Forward current vs. voltage drop per thyristor

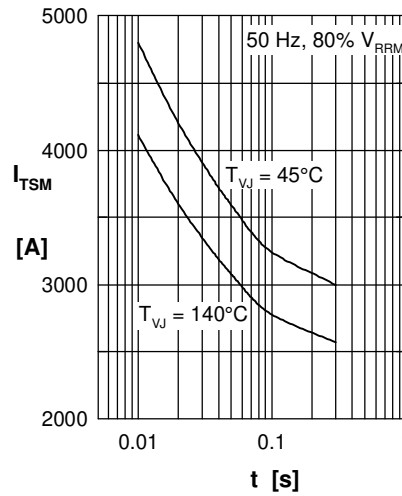


Fig. 2 Surge overload current vs. time per thyristor

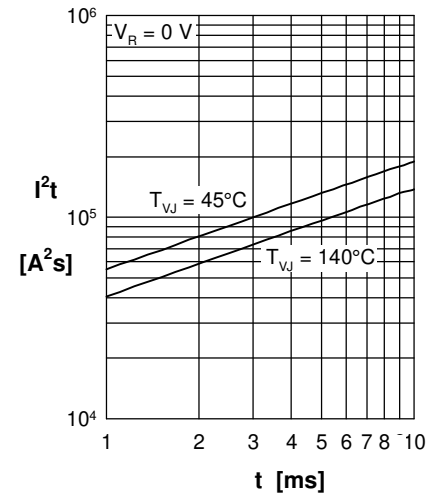
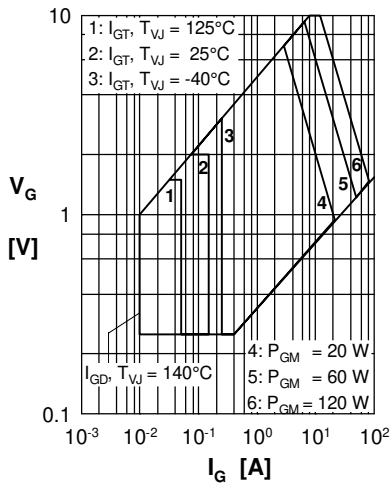

 Fig. 3  $I^2t$  vs. time per thyristor


Fig. 4 Gate voltage &amp; gate current

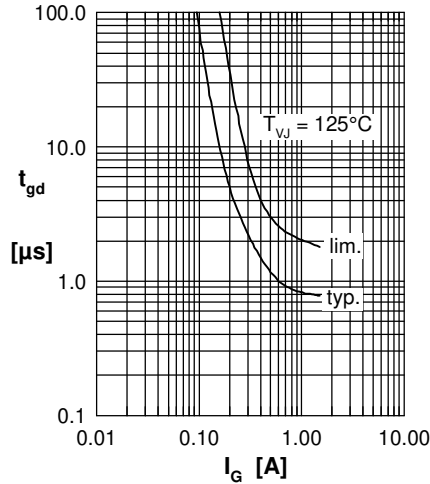
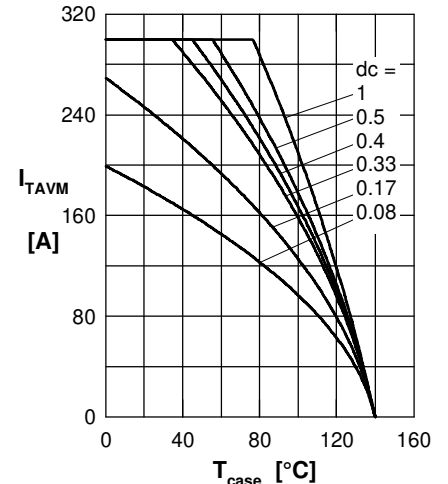

 Fig. 5 Gate controlled delay time  $t_{gd}$ 


Fig. 6 Max. forward current vs. case temperature per thyristor.

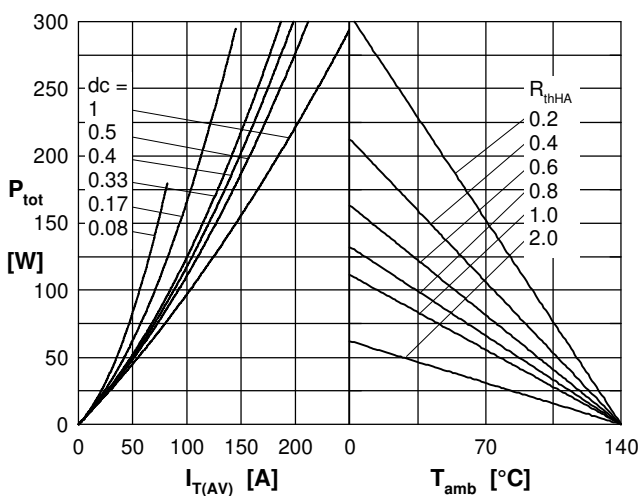


Fig. 7 Power dissipation vs. forward current and ambient temperature per thyristor

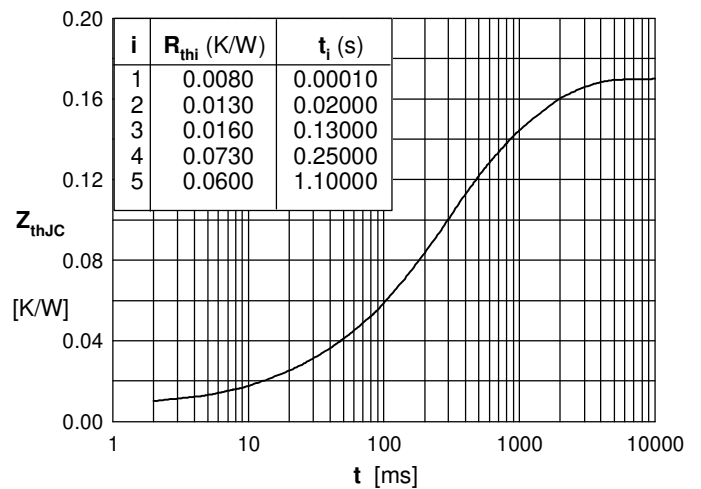


Fig. 8 Transient thermal impedance junction to case vs. time per thyristor